

Bidirectional heterostructures consisting of graphene and lateral MoS₂/WS₂ composites: first principles study

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Supplementary Information

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Figure S1 The calculated band structures of (MoS₂)_x/(WS₂)_{4-x} monolayer under different electric field intensity.

Figure S2 The configurations of G@(MoS₂)_x/(WS₂)_{4-x} (x = 0, 1, 2, 3, 4) heterobilayer.

Figure S3 The PDOS of MoS₂ and WS₂.

Figure S4. The band structure of G-MoS₂ at the GGA+U level.

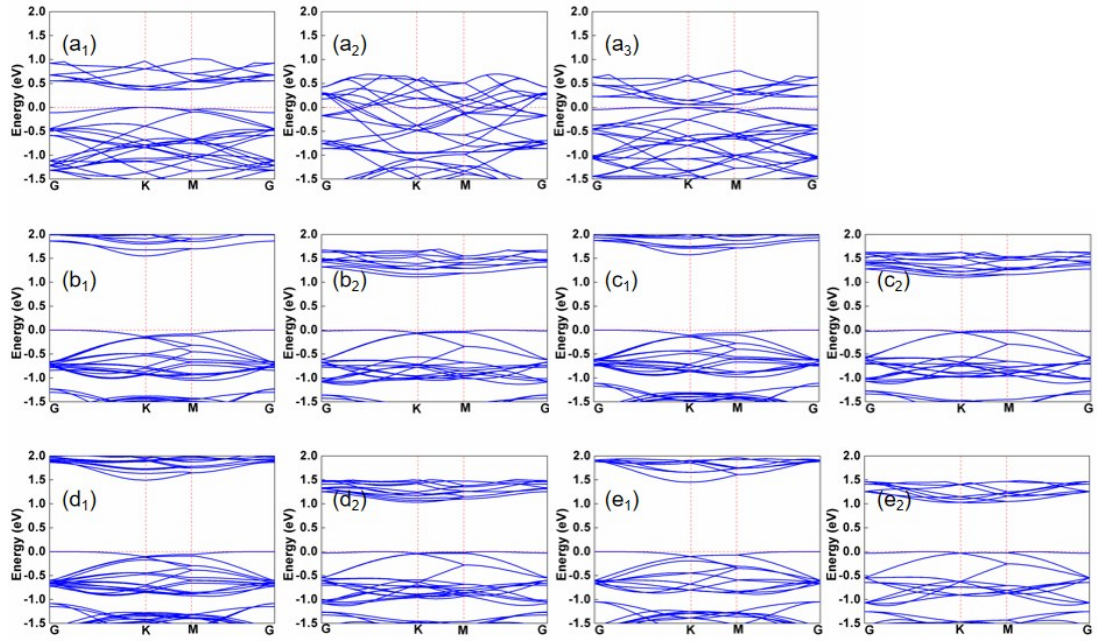


Figure S1. The band structures of WS_2 (a_{1-2}), $(\text{MoS}_2)_1/(\text{WS}_2)_3$ (b_{1-2}), $(\text{MoS}_2)_2/(\text{WS}_2)_2$ (c_{1-2}), $(\text{MoS}_2)_3/(\text{WS}_2)_1$ (d_{1-2}) and MoS_2 (e_{1-2}) under the electric field intensity at $F=0.5$ and 1.0 V \AA^{-1} (1-2), and a_3 is the band structure of WS_2 at $F=0.6 \text{ V \AA}^{-1}$. The horizontal red lines represent the Fermi level.

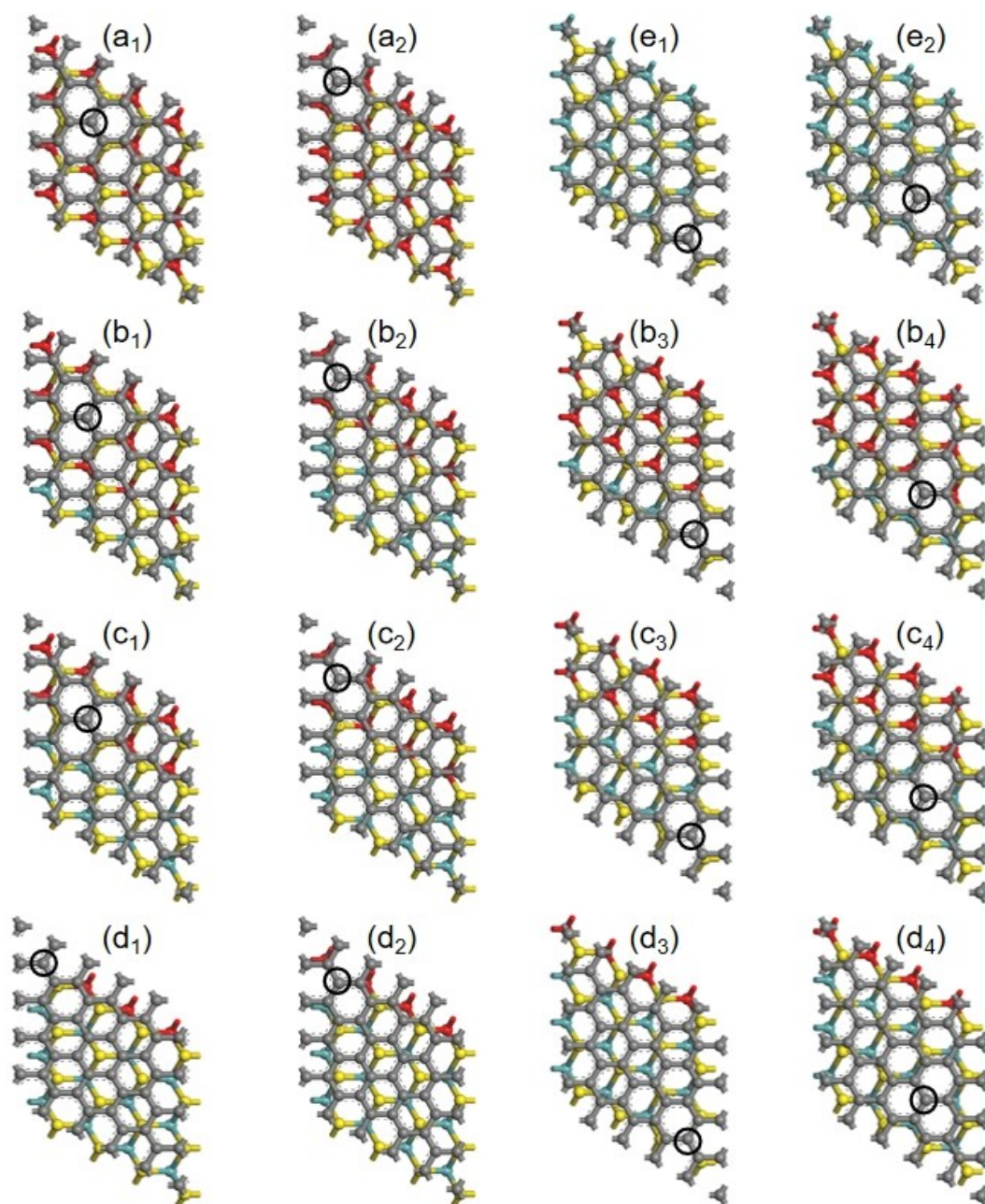


Figure S2. Top views of the configurations for $G@(\text{MoS}_2)_x/(\text{WS}_2)_{4-x}$ heterobilayer: $G@WS_2$ (a_{1-2}), $G@(\text{MoS}_2)_1/(\text{WS}_2)_3$ (b_{1-4}), $G@(\text{MoS}_2)_2/(\text{WS}_2)_2$ (c_{1-4}), $G@(\text{MoS}_2)_3/(\text{WS}_2)_1$ (d_{1-4}) and $G@MoS_2$ (e_{1-2}). The gray, yellow, green, and red balls denote C, S, Mo, W atoms, respectively.

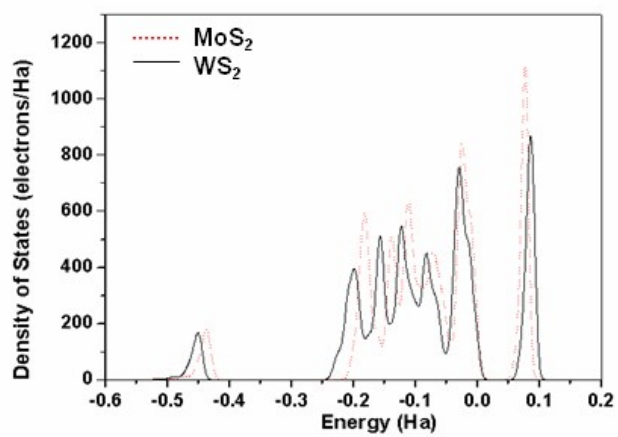


Figure S3. The PDOS of MoS₂ and WS₂.

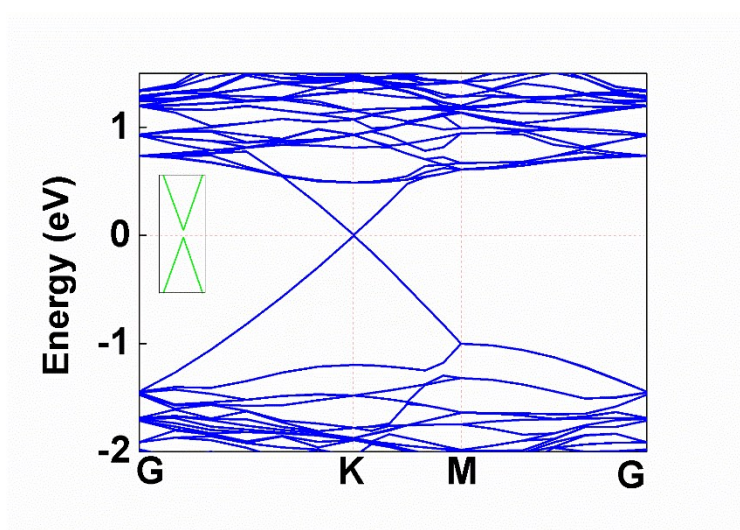


Figure S4. The band structure of G-MoS₂ at the GGA+U level.